

General Description

The WSR200N08 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSR200N08 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Product Summary

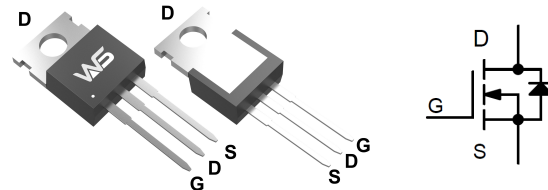
BV_{DSS}	$R_{DS(ON)}$	I_D
80V	2.9mΩ	200A

Applications

Switching application

Power Management for Inverter Systems.

TO-220FB-3L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	80	V
V_{GS}	Gate-Source Voltage	±25	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	200	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	144	A
I_{DM}	Pulsed Drain Current ² , $T_C=25^\circ C$	790	A
EAS	Avalanche Energy, Single pulse, $L=0.5mH$	1496	mJ
I_{AS}	Avalanche Current, Single pulse, $L=0.5mH$	200	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	345	W
$P_D@T_C=100^\circ C$	Total Power Dissipation ⁴	173	W
T_{STG}	Storage Temperature Range	-55 to 175	°C
T_J	Operating Junction Temperature Range	175	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62.5	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	0.43	°C/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	80	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.096	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =100A	---	2.9	3.5	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	2.0	3.0	4.0	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-5.5	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =80V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =80V, V _{GS} =0V, T _J =55°C	---	---	10	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±25V, V _{DS} =0V	---	---	±100	nA
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	3.2	---	Ω
Q _g	Total Gate Charge (10V)	V _{DS} =80V, V _{GS} =10V, I _D =30A	---	197	---	nC
Q _{gs}	Gate-Source Charge		---	31	---	
Q _{gd}	Gate-Drain Charge		---	75	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =50V, V _{GS} =10V, R _G =3Ω, I _D =30A	---	28	---	ns
T _r	Rise Time		---	18	---	
T _{d(off)}	Turn-Off Delay Time		---	42	---	
T _f	Fall Time		---	54	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	8154	---	pF
C _{oss}	Output Capacitance		---	1029	---	
C _{rss}	Reverse Transfer Capacitance		---	650	---	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy ⁵	V _{DD} =25V, L=0.5mH, I _{AS} =28A	160	---	---	mJ

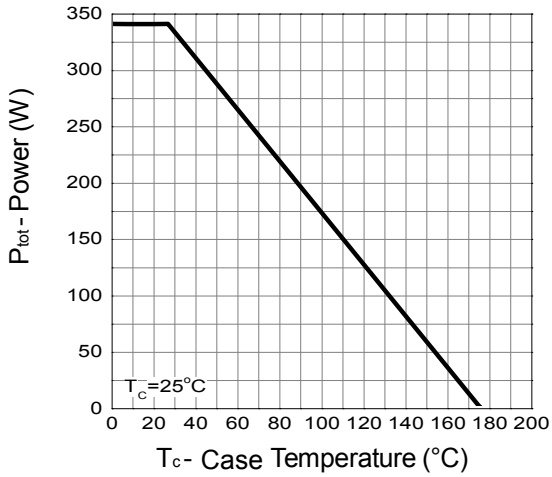
Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	V _G =V _D =0V, Force Current	---	---	200	A
I _{SM}	Pulsed Source Current ^{2,6}		---	---	350	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =15A, T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	I _F =15A, dI/dt=100A/μs, T _J =25°C	---	30	---	nS
Q _{rr}	Reverse Recovery Charge		---	52	---	nC

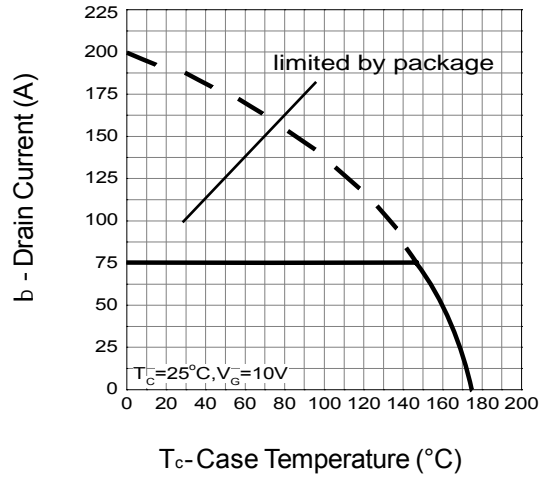
Note * : Pulse test ; pulse width ≤300μs, duty cycle ≤2%.

Typical Operating Characteristics

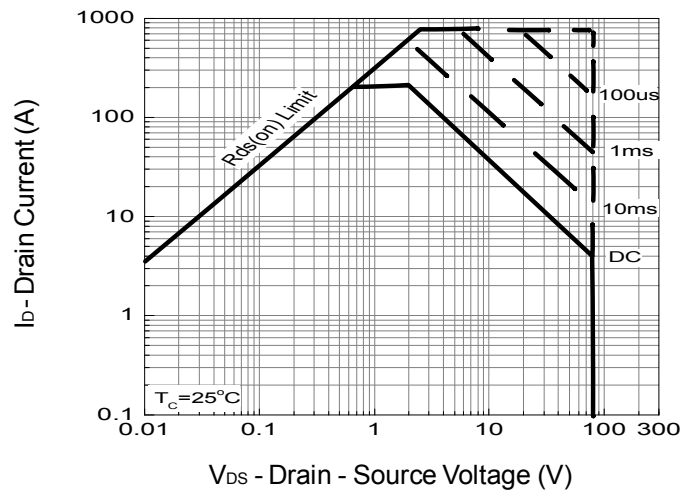
Power Dissipation



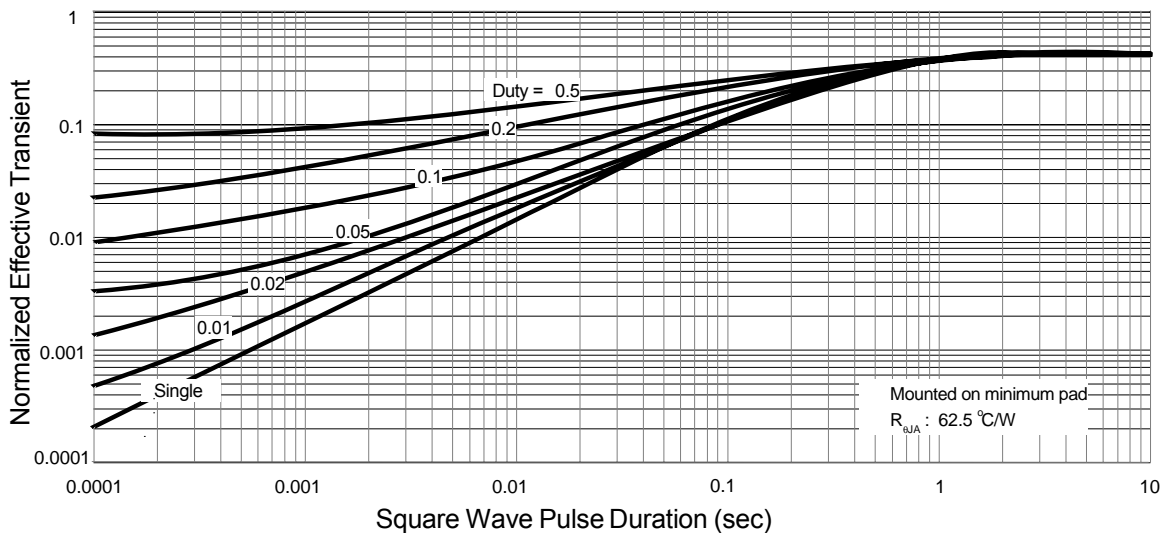
Drain Current



Safe Operation Area

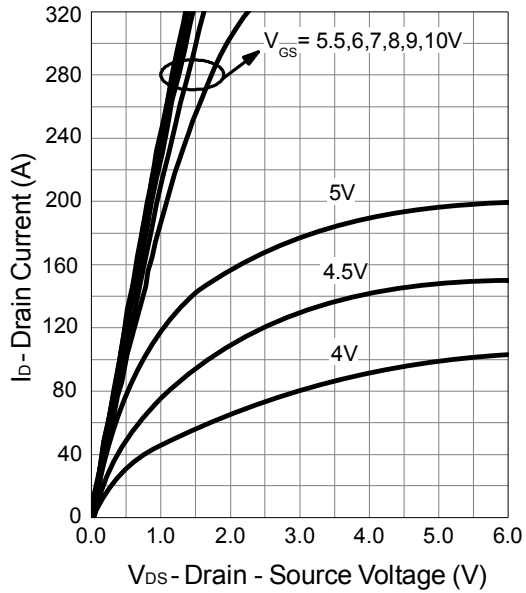


Thermal Transient Impedance

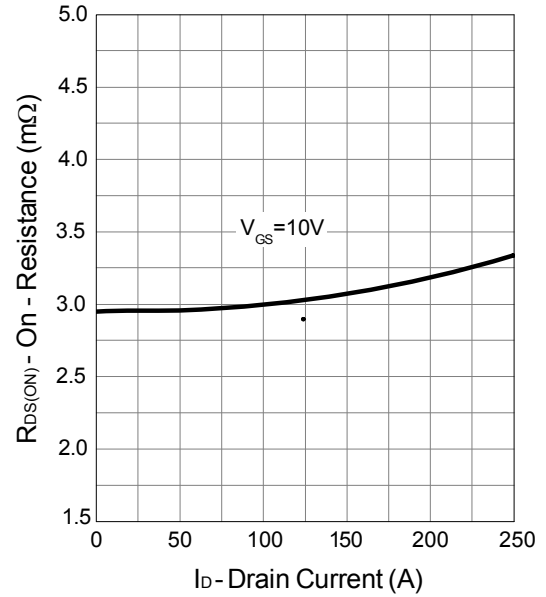


Typical Operating Characteristics (Cont.)

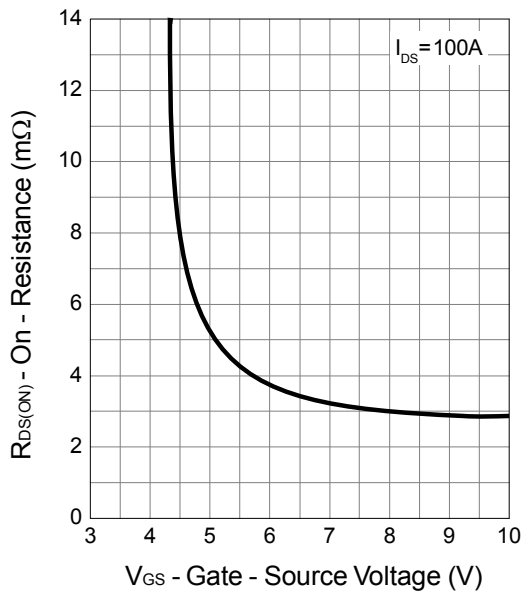
Output Characteristics



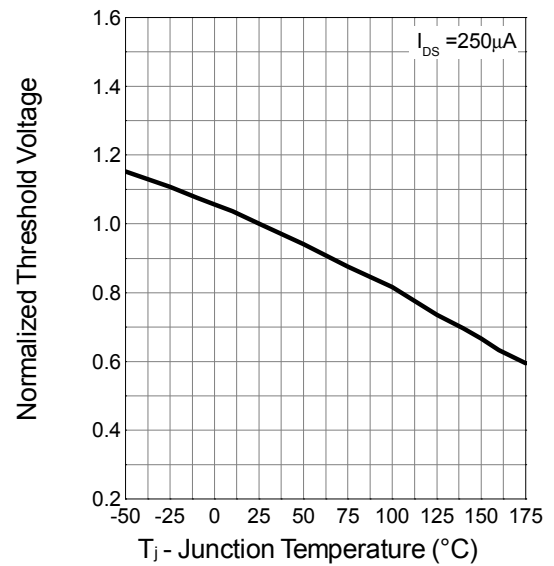
Drain-Source On Resistance



Gate-Source On Resistance

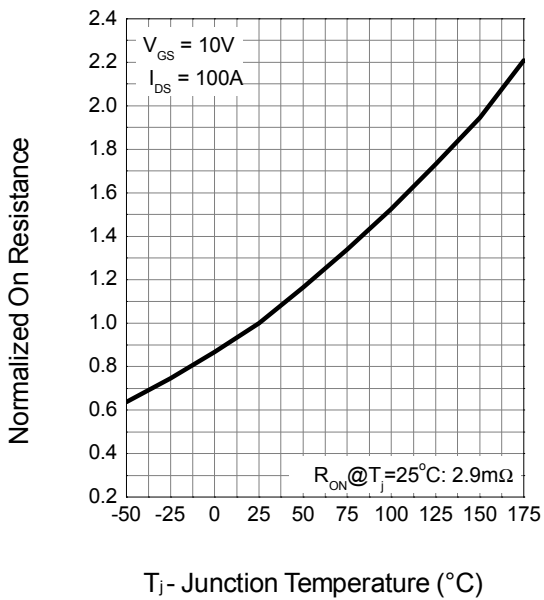


Gate Threshold Voltage

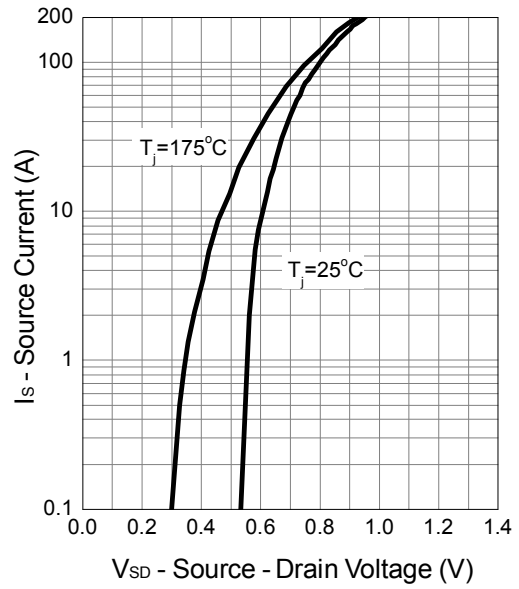


Typical Operating Characteristics (Cont.)

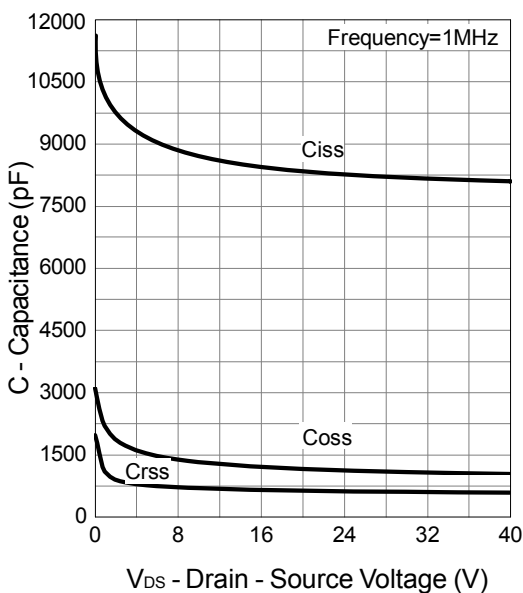
Drain-Source On Resistance



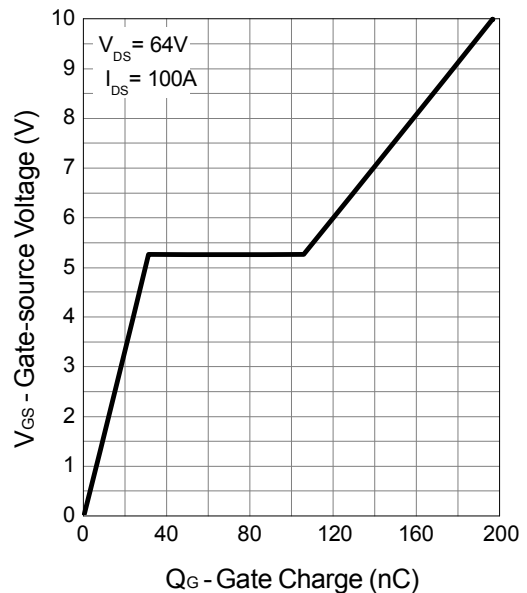
Source-Drain Diode Forward



Capacitance



Gate Charge





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